

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Substitute for form 1449/PTO)				ATTY. DOCKET NO. <b>061282-0234</b>		SERIAL NO. <b>10/574,863</b>	
				APPLICANT <b>Yuichiro SASAKI, et al.</b>			
				FILING DATE <b>April 06, 2006</b>		GROUP <b>2823</b>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		US 5,915,196	06-22-1999	MINEJI			
		US 6,153,524	11-28-2000	HENLEY et al.			
		US 6,159,810	12-12-2000	YANG			
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		US 5,407,845	04-18-1995	NASU et al.	Corresponds to JP 2530990 B2		
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<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code <sup>3</sup> -Number 4-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No	
		<del>WO 03/014979 A</del>	02-20-2003	APPLIED MATERIALS, INC.		X	
		<del>JP 2530990 B2</del>	09-04-1996	FUJITSU LTD	Corresponds to US 5,407,845		X
		<del>JP 03-218638</del>	09-26-1991	SEIKO INSTR INC		JAPAN (w/English Abstract)	
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<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		International Search Report issued in International Patent Application No. PCT/JP2005/009949 dated July 5, 2005					
		International Search Report issued in International Patent Application No. PCT/JP2004015308 mailed January 18, 2005					
		Japanese Notification of Reasons for Refusal, w/ English translation thereof, issued in Japanese Patent Application No. JP 2005-502685 dated May 19, 2009					
		European Search Report issued in European Patent Application No. EP 04710478 dated May 12, 2009					
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		<b>US 2002/0006689 A1</b>	<b>01-17-2002</b>	<b>MIYASAKA, MITSUTOSHI</b>			
<b>FOREIGN PATENT DOCUMENTS</b>							
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		<del>JP 7-142421</del>	<del>06-02-1995</del>	<del>NIPPON ELECTRIC CO</del>			<del>JAPAN (w/English Abstract)</del>
		<del>JP 2003-86529</del>	<del>03-20-2003</del>	<del>DENSO CORP</del>			<del>JAPAN (w/English Abstract)</del>
		<del>JP 2003-7686</del>	<del>01-10-2003</del>	<del>SONY CORP</del>			<del>JAPAN (w/English Abstract)</del>
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		<del>JP 2000-12481</del>	<del>01-14-2000</del>	<del>APPLIED MATERIALS INC</del>			<del>JAPAN (w/English Abstract)</del>
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<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
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		<del>R. SIEGELE, et al., "Helium Bubbles in silicon: Structure and Optical properties," Appl. Phys. Lett. 66 (11), 13 March 1995, pp. 1319-1321</del>					
		<del>V.F. REUTOV &amp; A.S. SOKHATSKII, "Helium Ion Bombardment Induced Amorphization of Silicon Crystals," Technical Physics Letters, Vol. 38, No. 7, 2002, pp. 615-617</del>					
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